

## High Speed CMOS Logic Quad Buffer, Three-State

### Features

- Three-State Outputs
- Separate Output Enable Inputs
- Fanout (Over Temperature Range)
  - Standard Outputs . . . . . 10 LSTTL Loads
  - Bus Driver Outputs . . . . . 15 LSTTL Loads
- Wide Operating Temperature Range . . . -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
  - 2V to 6V Operation
  - High Noise Immunity:  $N_{IL} = 30\%$ ,  $N_{IH} = 30\%$  of  $V_{CC}$  at  $V_{CC} = 5V$
- HCT Types
  - 4.5V to 5.5V Operation
  - Direct LSTTL Input Logic Compatibility,  $V_{IL} = 0.8V$  (Max),  $V_{IH} = 2V$  (Min)
  - CMOS Input Compatibility,  $I_I \leq 1\mu A$  at  $V_{OL}$ ,  $V_{OH}$

### Description

The 'HC125 and 'HCT125 contain 4 independent three-state buffers, each having its own output enable input, which when "HIGH" puts the output in the high impedance state.

### Ordering Information

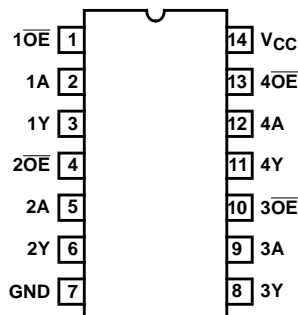
PART NUMBER	TEMP. RANGE (°C)	PACKAGE
CD54HC125F	-55 to 125	14 Ld CERDIP
CD54HC125F3A	-55 to 125	14 Ld CERDIP
CD74HC125E	-55 to 125	14 Ld PDIP
CD74HC125M	-55 to 125	14 Ld SOIC
CD54HCT125F3A	-55 to 125	14 Ld CERDIP
CD74HCT125E	-55 to 125	14 Ld PDIP
CD74HCT125M	-55 to 125	14 Ld SOIC

#### NOTES:

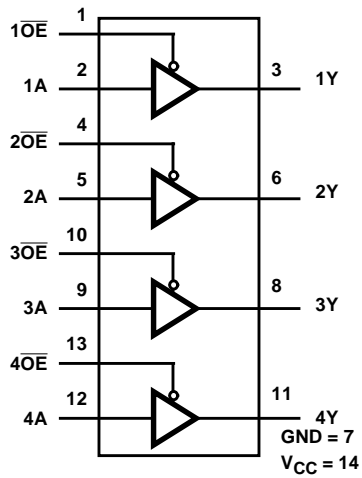
1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
2. Wafer and die for this part number is available which meets all electrical specifications. Please contact your local TI sales office or customer service for ordering information.

### Pinout

CD54HC125, CD54HCT125  
(CERDIP)  
CD74HC125, CD74HCT125  
(PDIP, SOIC)  
TOP VIEW



**Functional Diagram**

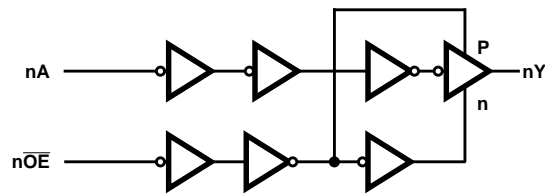


TRUTH TABLE

INPUTS		OUTPUTS
nA	nOE	nY
H	L	H
L	L	L
X	H	Z

NOTE:  
 H = High Voltage Level  
 L = Low Voltage Level  
 X = Don't Care  
 Z = High Impedance, OFF State

**Logic Diagram**



## CD54/74HC125, CD54/74HCT125

### Absolute Maximum Ratings

DC Supply Voltage, $V_{CC}$ .....	-0.5V to 7V
DC Input Diode Current, $I_{IK}$	
For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$ .....	$\pm 20mA$
DC Output Diode Current, $I_{OK}$	
For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$ .....	$\pm 20mA$
DC Drain Current, per Output, $I_O$	
For $-0.5V < V_O < V_{CC} + 0.5V$ .....	$\pm 35mA$
DC Output Source or Sink Current per Output Pin, $I_O$	
For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$ .....	$\pm 25mA$
DC $V_{CC}$ or Ground Current, $I_{CC}$ .....	$\pm 70mA$

### Thermal Information

Thermal Resistance (Typical, Note 3)	$\theta_{JA}$ (°C/W)
PDIP Package .....	90
SOIC Package .....	175
Maximum Junction Temperature .....	150°C
Maximum Storage Temperature Range .....	-65°C to 150°C
Maximum Lead Temperature (Soldering 10s) .....	300°C
(SOIC - Lead Tips Only)	

### Operating Conditions

Temperature Range ( $T_A$ ) .....	-55°C to 125°C
Supply Voltage Range, $V_{CC}$	
HC Types .....	.2V to 6V
HCT Types .....	4.5V to 5.5V
DC Input or Output Voltage, $V_I, V_O$ .....	0V to $V_{CC}$
Input Rise and Fall Time	
2V .....	1000ns (Max)
4.5V .....	500ns (Max)
6V .....	400ns (Max)

*CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.*

#### NOTE:

3.  $\theta_{JA}$  is measured with the component mounted on an evaluation PC board in free air.

### DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		$V_{CC}$ (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		$V_I$ (V)	$I_O$ (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
<b>HC TYPES</b>												
High Level Input Voltage	$V_{IH}$	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	$V_{IL}$	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	$V_{OH}$	$V_{IH}$ or $V_{IL}$	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads	$V_{OH}$	$V_{IH}$ or $V_{IL}$	-6	4.5	3.98	-	-	3.84	-	3.7	-	V
			-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	$V_{OL}$	$V_{IH}$ or $V_{IL}$	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads	$V_{OL}$	$V_{IH}$ or $V_{IL}$	6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	$I_I$	$V_{CC}$ or GND	-	6	-	-	$\pm 0.1$	-	$\pm 1$	-	$\pm 1$	$\mu A$

**CD54/74HC125, CD54/74HCT125**

**DC Electrical Specifications (Continued)**

PARAMETER	SYMBOL	TEST CONDITIONS		V <sub>CC</sub> (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V <sub>I</sub> (V)	I <sub>O</sub> (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Quiescent Device Current	I <sub>CC</sub>	V <sub>CC</sub> or GND	0	6	-	-	8	-	80	-	160	μA
Three-State Leakage Current	I <sub>OZ</sub>	V <sub>IL</sub> or V <sub>IH</sub>	-	6	-	-	±0.5	-	±5	-	±10	μA
<b>HCT TYPES</b>												
High Level Input Voltage	V <sub>IH</sub>	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V <sub>IL</sub>	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V <sub>OH</sub>	V <sub>IH</sub> or V <sub>IL</sub>	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V <sub>OL</sub>	V <sub>IH</sub> or V <sub>IL</sub>	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I <sub>I</sub>	V <sub>CC</sub> to GND	0	5.5	-	-	±0.1	-	±1	-	±1	μA
Quiescent Device Current	I <sub>CC</sub>	V <sub>CC</sub> or GND	0	5.5	-	-	8	-	80	-	160	μA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load (Note 4)	ΔI <sub>CC</sub>	V <sub>CC</sub> -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μA
Three-State Leakage Current	I <sub>OZ</sub>	V <sub>IL</sub> or V <sub>IH</sub>	-	5.5	-	-	±0.5	-	±5	-	±10	μA

NOTE:

4. For dual-supply systems theoretical worst case (V<sub>I</sub> = 2.4V, V<sub>CC</sub> = 5.5V) specification is 1.8mA.

**HCT Input Loading Table**

INPUT	UNIT LOADS
nA, nOE	1

NOTE: Unit Load is ΔI<sub>CC</sub> limit specified in DC Electrical Specifications table, e.g., 360μA max at 25°C.

## CD54/74HC125, CD54/74HCT125

### Switching Specifications Input $t_r, t_f = 6\text{ns}$

PARAMETER	SYMBOL	TEST CONDITIONS	$V_{CC}$ (V)	25°C		-40°C TO 85°C	-55°C TO 125°C	UNITS
				TYP	MAX	MAX	MAX	
<b>HC TYPES</b>								
Propagation Delay Time nA to nY	$t_{PLH}, t_{PHL}$	$C_L = 50\text{pF}$	2	-	100	125	150	ns
			4.5	-	20	25	30	ns
		$C_L = 15\text{pF}$	5	8	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	17	21	26	ns
Enable Delay Time	$t_{PZL}, t_{PZH}$	$C_L = 50\text{pF}$	2	-	125	155	190	ns
			4.5	-	25	31	38	ns
		$C_L = 15\text{pF}$	5	10	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	21	26	32	ns
Disable Delay Time	$t_{PLZ}, t_{PHZ}$	$C_L = 50\text{pF}$	2	-	125	155	190	ns
		$C_L = 50\text{pF}$	4.5	-	25	31	38	ns
		$C_L = 15\text{pF}$	5	10	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	21	26	32	ns
Output Transition Time	$t_{TLH}, t_{THL}$	$C_L = 50\text{pF}$	2	-	60	75	90	ns
			4.5	-	12	15	18	ns
			6	-	10	13	15	ns
Input Capacitance	$C_I$	-	-	-	10	10	10	pF
Three-State Output Capacitance	$C_O$	-	-	-	20	20	20	pF
Power Dissipation Capacitance (Notes 5, 6)	$C_{PD}$	-	5	29	-	-	-	pF
<b>HCT TYPES</b>								
Propagation Delay Time nA to nY	$t_{PLH}, t_{PHL}$	$C_L = 50\text{pF}$	4.5	-	25	31	38	ns
		$C_L = 15\text{pF}$	5	10	-	-	-	ns
Output Enable Time	$t_{PZL}, t_{PZH}$	$C_L = 50\text{pF}$	4.5	-	25	31	38	ns
		$C_L = 15\text{pF}$	5	10	-	-	-	ns
Output Disabling Time	$t_{PLZ}, t_{PHZ}$	$C_L = 50\text{pF}$	4.5	-	28	35	42	ns
		$C_L = 15\text{pF}$	5	11	-	-	-	ns
Output Transition Times	$t_{TLH}, t_{THL}$	$C_L = 50\text{pF}$	4.5	-	12	15	18	ns
Input Capacitance	$C_I$	-	-	-	10	10	10	pF
Three-State Output Capacitance	$C_O$	-	-	-	20	20	20	pF
Power Dissipation Capacitance (Notes 5, 6)	$C_{PD}$	-	5	34	-	-	-	pF

**NOTES:**

5.  $C_{PD}$  is used to determine the dynamic power consumption, per channel.
6.  $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$  where  $f_i$  = Input Frequency,  $f_O$  = Output Frequency,  $C_L$  = Output Load Capacitance,  $V_{CC}$  = Supply Voltage.

Test Circuits and Waveforms



FIGURE 1. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC



FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

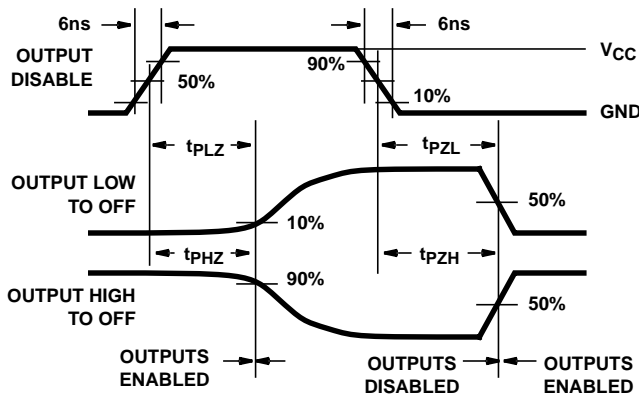


FIGURE 3. HC THREE-STATE PROPAGATION DELAY WAVEFORM

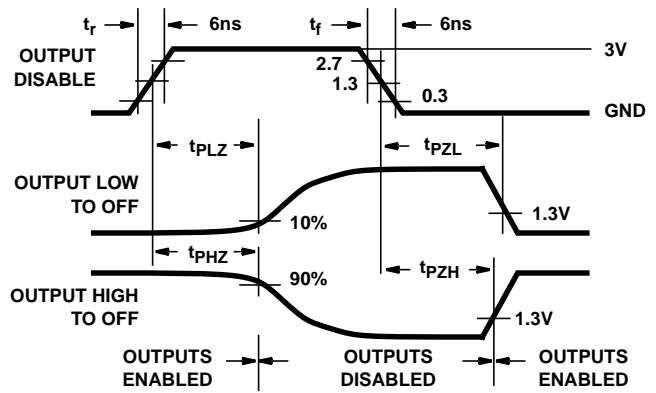
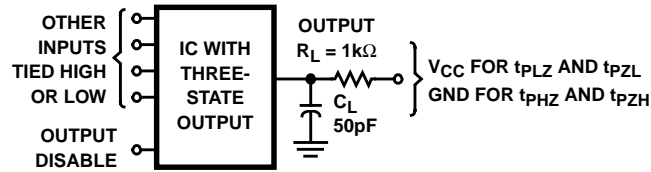


FIGURE 4. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms  $t_{PLZ}$  and  $t_{PZL}$  are the same as those for three-state shown on the left. The test circuit is Output  $R_L = 1k\Omega$   $V_{CC}$ ,  $C_L = 50pF$ .

FIGURE 5. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT

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